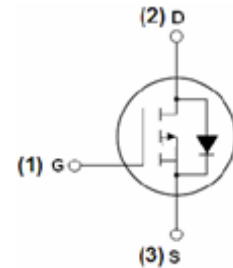


Trench P-Channel PowerMOSFET Wafer Datasheet

FEATURES

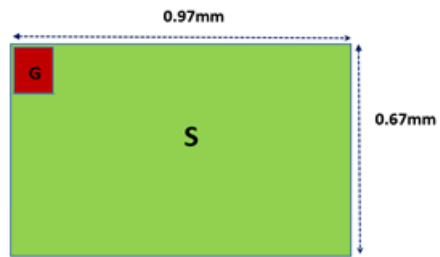
- -30V、4.5A* , P-channel
- $R_{DS(on)}=65m\Omega(MAX)$
- Ultra low Q_{gd}
- Fast switching



Electrical Characteristics($T_J=25^{\circ}C$)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30			V	$V_{GS}=0V, I_D=-250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance		50	65	$m\Omega$	$V_{GS}=-10V, I_D=-2A$
			65	85	$m\Omega$	$V_{GS}=-4.5V, I_D=-2A$
$V_{GS(th)}$	Gate Threshold Voltage	0.7		1.4	V	$V_{DS}=V_{GS}, I_D=-250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=-30V, V_{GS}=0V, T_J=25^{\circ}C$
I_{GSS}	Gate-Body Leakage Current			± 100	nA	$V_{GS}=\pm 18V$
V_{SD}	Body Diode Voltage			1.5	V	$V_{GS}=0V, I_{SD}=-4.5A$
T_J, T_{stg}	Operating and Storage Temperature Range	-55~+125			$^{\circ}C$	

Mechanical Data

Die Size	970×670	μm^2	
Gate Pad Size	150×150		
Source Pad Size	No Passivation		
Scribe Line Size	50	μm	
Wafer Diameter	200	mm	
Wafer Thickness	175	μm	
Passivation Frontside	No Passivation	---	
Source Metallization	AlCu , 4.0	μm	
Drain Metallization	Ti-Ni-Ag , 1K-2K-10K	A	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in desiccated nitrogen, with no contamination		

* Electrical characteristics are reported for the reference packaged part (SOT23\SOP8) and can not be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.